

**AMENDMENTS TO THE CLAIMS**

1-11 (canceled)

12 (New). A semiconductor device, comprising:

an inner region including an SRAM section and/or a logic circuit section, and having MOS transistors operating at a first voltage; and

an outer region including an interface section and located outside of the inner region, wherein

    said interface section comprises first MOS transistors operating at the first voltage and second MOS transistors operating at a second voltage higher than the first voltage and performing direct signal transmission and reception to and from an external device

    said first MOS transistors each have a channel-forming semiconductor region formed of a first well, and

    said second MOS transistors each have a channel-forming semiconductor region formed of a second well deeper than the first well.